

VOLTAGE RANGE: 45V

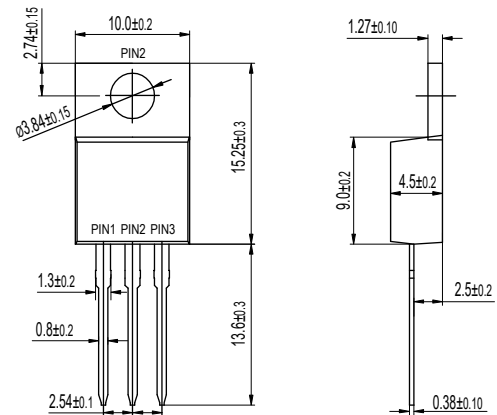
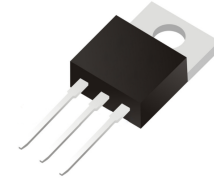
CURRENT: 10A

Features

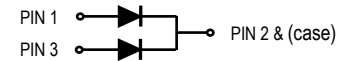
- Ultra low v_f
- High efficiency operation
- Low power loss
- Low stored charge majority carrier conduction
- High forward surge capability
- Lead free in compliance with EU RoHS 2011/65/EU directive

Mechanical Data

- Circuit figure: Common cathode
- Leads: Solderable per mil-std-202, Method 208
- Polarity: as marked
- Mounting torque: 5 in-lbs maximum
- Terminals: Puretin plated
- Weight: TO-220AB 1.85 grams



TO-220AB



Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise specified

RATINGS	SYMBOL	SBL1045CT	UNIT
Maximum repetitive reverse voltage	VRRM	45	V
Maximum RMS voltage	VRMS	31.5	V
Maximum DC blocking voltage	VDC	45	V
Maximum average forward current per device per diode	I _{AV}	10 5	A
Peak forward surge current, 8.3ms single half sine-wave superimposed on rated load	I _{FSM}	120	A
Typical thermal resistance per diode (Note 1)	R _{θ-JC}	2.0	°C/W
Operating junction temperature range	T _J	-55 to +150	°C
Storage temperature range	T _{STG}	-55 to +150	°C

Notes: 1. Thermal resistance from junction to case.

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Breakdown voltage per diode	V_{BR}	$I_R=0.5\text{mA}$	45	-	-	V
Instantaneous forward voltage per diode	V_F	$I_F=5\text{A}$ $T_J=25^\circ\text{C}$	-	-	0.50	V
		$I_F=5\text{A}$ $T_J=125^\circ\text{C}$	-	-	0.46	V
Reverse current per diode	I_R	$V_R=45\text{V}$ $T_J=25^\circ\text{C}$	-	-	200	μA
		$V_R=45\text{V}$ $T_J=125^\circ\text{C}$	-	-	100	mA

FIG. 1 - TYPICAL FORWARD CURRENT DERATING CURVE

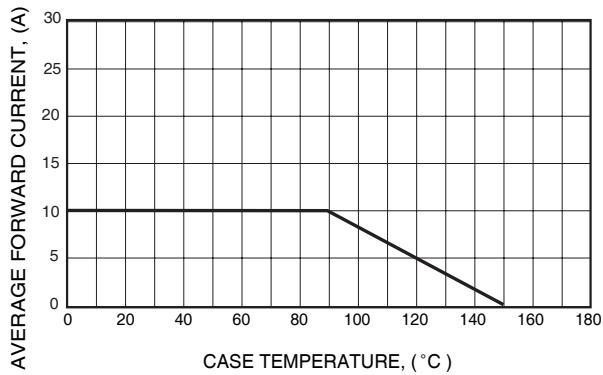


FIG. 2 - MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

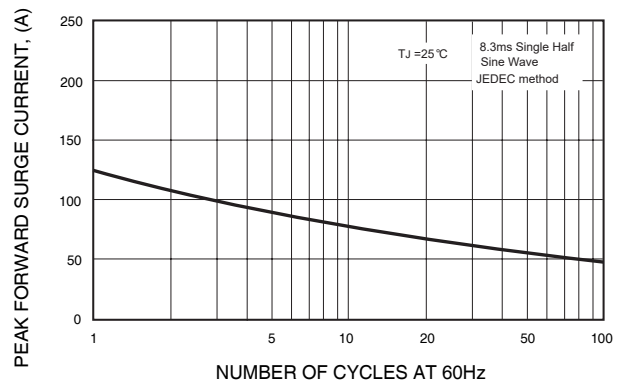


FIG. 3 - TYPICAL REVERSE CHARACTERISTICS

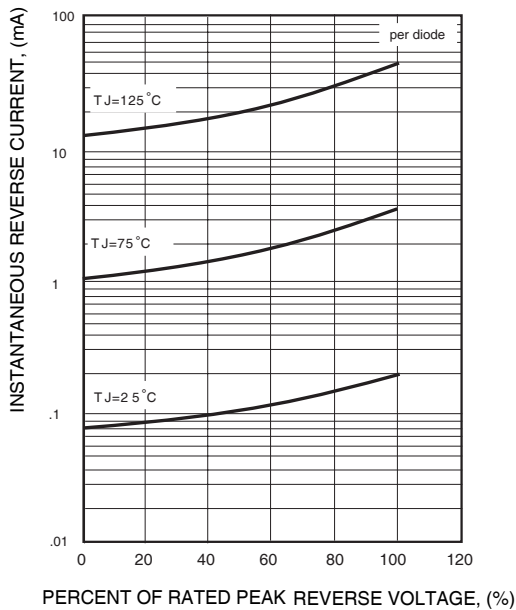


FIG. 4 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

